

# DUAL POWER SCHOTTKY RECTIFIERS

## 60A Pk, 45V

USD335C  
 USD345C  
 USD335CHR2  
 USD345CHR2

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### FEATURES

- Very Low Forward Voltage
- Low Recovered Charge
- Rugged Package Design (TO-3)
- High Efficiency for Low Voltage Supplies
- 45V Blocking @ Rated  $T_{jmax}$
- 50V Repetitive Surge Voltage
- Dual Schottky Rectifier in a Single Package

### DESCRIPTION

The USD320C series has two Schottky barriers arranged in a common cathode configuration and is ideally suited for a full wave output rectifier in low voltage switching power supplies.

### ABSOLUTE MAXIMUM RATINGS (Total for USD300C Series)

Average Rectified Forward Current,  $I_O$  @  $T_C = 100^\circ\text{C}$  ..... 30A.....

### ABSOLUTE MAXIMUM RATINGS (Per Diode)

	USD335C USD335CHR2	USD345C USD345CHR2
Working Peak Reverse Voltage $V_{RWM}$ .....	35V	45V
DC Blocking Voltage, $V_R$ .....	35V	45V
Peak Repetitive Surge Voltage, $V_{RSM}$ @ $I_{RM}$ .....	42V	54V
Average Rectified Forward Current, $I_O$ .....	30A in full wave configuration*	
Non-repetitive Peak Surge current (8.3 mS), $I_{FSM}$ .....	500A	
Peak Reverse Transient Current, $I_{RM}$ .....	2A	
Storage Temperature Range, $T_{stg}$ .....	-55°C to +200°C	
Peak Operating Junction Temperature, $T_{jmax}$ .....	175°C	
Thermal Resistance, Junction to Case, $R_{\theta JC}$ .....	1.4°C/W	

\* Each Anode Pin Limited to 18A Average.  
 Package Capability 30A Average.

### ELECTRICAL CHARACTERISTICS ( $T_{CASE} = 25^\circ\text{C}$ )

Characteristic	Symbol	Limit	Units	Conditions
Maximum Instantaneous Reverse Current	$i_R$	10 50	mA mA	$T_C = 25^\circ\text{C}$ , $V_R = V_{RWM}$ $T_C = 125^\circ\text{C}$ Pulse Width = 400 $\mu\text{S}$ Duty Cycle = 1 percent
Maximum Instantaneous Forward Voltage	$V_F$	0.57 0.66 0.60	V V V	$i_F = 10\text{A}$ , $T_C = 25^\circ\text{C}$ $i_F = 20\text{A}$ , $T_C = 25^\circ\text{C}$ $i_F = 20\text{A}$ , $T_C = 125^\circ\text{C}$ Pulse Width = 300 $\mu\text{S}$ Duty Cycle = 1 percent
Capacitance	$C_t$	2000	pF	$V_R = 5.0\text{V}$
Voltage Rate of Change	$dv/dt$	1000	v/ $\mu\text{S}$	$V_R = V_{RWM}$

### MECHANICAL SPECIFICATIONS

**NOTE:**  
 Leads may be soldered to within  $1/16"$  of base provided temperature-time exposure is less than 260°C for 10 seconds.

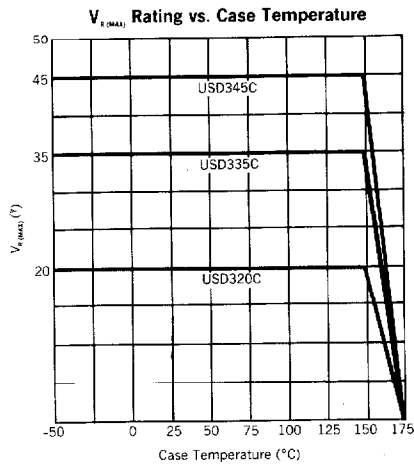
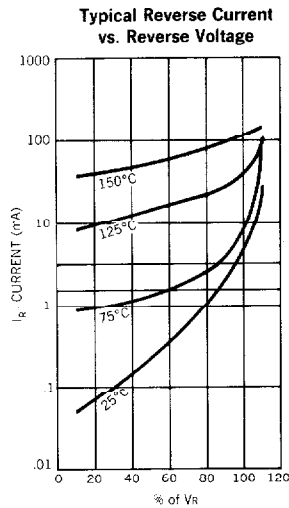
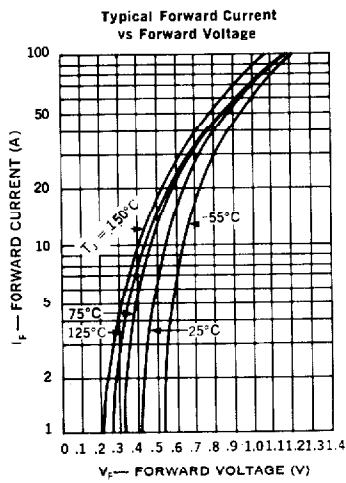
**USD300C SERIES**  
**USD300CHR2 SERIES**

	ins.	mm.
A	.875 MAX.	22.23 MAX.
B	.135 MAX.	3.43 MAX.
C	.250-.450	6.35-11.43
D	.312 MIN.	7.92 MIN.
E	.038-.043 DIA.	0.97-1.09 DIA.
F	.188 MAX. RAD.	4.78 MAX. RAD.
G	1.177-1.197	29.90-30.40
H	.655-.675	16.64-17.15
J	.205-.225	5.21-5.72
K	.420-.440	10.67-11.18
L	.525 MAX. RAD.	13.34 MAX. RAD.
M	.151-.161 DIA.	3.84-4.09 DIA.

**TO-204AA (TO-3)**

Notes: All metal surfaces tin plated.

**Microsemi Corp.**  
**Watertown**  
 The diode experts



**OPTIONAL HIGH RELIABILITY (HR2) SCREENING**

The following tests are performed on 100% of the devices specified USD335CHR2, 345CHR2.

SCREEN	MIL-STD-750 METHOD	CONDITIONS
1. High temperature	1032	241 hours @ T <sub>A</sub> = 150°C
2. Temperature Cycle	1051	F, 20 Cycles, -55 to +150°C. No dwell required @ 25°C, t ≥ 10 min. @ extremes
3. Hermetic Seal a. Fine Leak b. Gross Leak	1071	H, Helium C, Liquid
4. Thermal Impedance		Sage Test
5. Interim Electrical Parameters	GO/NO GO	V <sub>F</sub> and I <sub>R</sub> @ 25°C
6. High Temperature Reverse Blocking	Similar to Method 1040	½ Sine Reverse, t = 48 Hours, T <sub>C</sub> = 125°C, VRW <sub>M</sub> = rating, F = 50-60 Hz, I <sub>O</sub> = OA
7. Final Electrical Parameters	GO/NO GO	V <sub>F</sub> + I <sub>R</sub> @ 25°C PDA = 10% (Final Electricals)